### DISTINCTIVE CHARACTERISTICS

- Internal resistors eliminate need for external series resistors and reduce package count
- Guaranteed maximum undershoot of -0.5 V on **HIGH-to-LOW** transition
- Glitch-free outputs during power-up and power-down
- Simple "flow-through" pinout

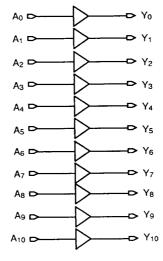
- Large capacitive drive capability (up to 88 DRAMs) designed to drive 16K, 64K, 256K, 1M and 4M dynamic-memory arrays
- 24-pin, 0.3-inch space-saving plastic dual In-line package and 28-pin plastic leaded chip carrier

### **GENERAL DESCRIPTION**

The Am2976 is an 11-bit bipolar Dynamic RAM Driver designed to drive the capacitive input characteristics of the address and control lines of 64K, 256K, 1M and 4M MOS dynamic RAMs. This device has non-inverting drivers and is functionally similar to the Am2966, but contains eleven drivers to accommodate wider address paths. A significant performance advantage of the increase in drivers per device is the ability to combine more signals onto a single device, thus minimizing skew time between drivers (i.e., RAS and CAS).

The architecture of the lower output driver includes an internal collector-resistor to control undershoot (not to exceed -0.5 V) on the HIGH-to-LOW transition. This design also allows for control of the output fall time without slowing the output rise. The upper output driver pulls up to 2.7 V minimum to be compatible with MOS memory and is designed to have a rise time symmetrical with the low output's controlled fall times. The output impedance, 25 ohms nominal, is identical in both the logic HIGH and LOW states - this value was selected to match the intrinsic impedance of a PC board trace. The inclusion of internal resistors eliminates the need for additional external series resistors, therefore reducing package count and saving board area.

#### LOGIC DIAGRAM

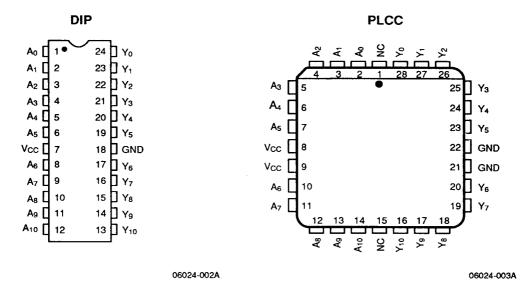


06024-001A

Publication# 06024 Rev. D Amendment /0

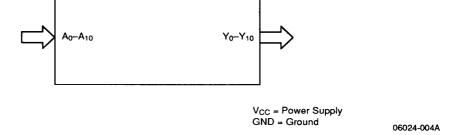
issue Date: January 1990

# **CONNECTION DIAGRAMS**



Note: Pin 1 is marked for orientation.

# LOGIC SYMBOL



# **RELATED AMD PRODUCTS**

Part No.	Description			
Am29368	1M Dynamic Memory Controller/Driver			
Am29C60A	High Speed CMOS Cascadable 16-Bit EDC			
Am29C660D	12 ns CMOS Cascadable 32-Bit EDC			
Am29C668	4M Configurable Dynamic Memory Controller/Driver			
Am2968A	256K Dynamic Memory Controller/Driver			
Am29C983A	9-Bit x 4-Port Multiple Bus Exchange, High Speed			
Am29C985	9-Bit x 4-Port Multiple Bus Exchange with Parity			
Am2965/6	8-Bit Dynamic RAM Driver Inverting/Non-Inverting			

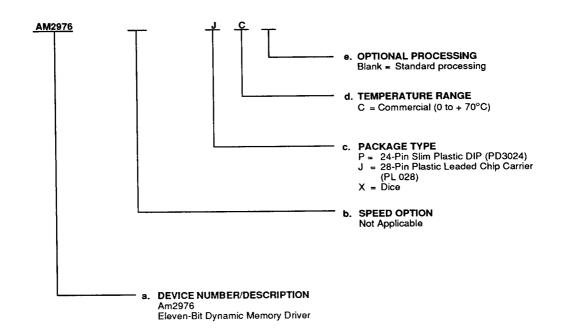
6-142 Am2976

# **ORDERING INFORMATION Standard Products**

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

a. Device Number

- b. Speed Option (if applicable)
- c. Package Type d. Temperature Range
- e. Optional Processing



Valid Combinations				
AM2976	PC, JC, XC			

### Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, and to check on newly released valid combinations.

## PIN DESCRIPTION

A<sub>0</sub>-A<sub>10</sub>

Driver (Address) Input (Inputs --- 11)

These eleven pins are the inputs to the driver.

Y0-Y10

Driver (General Control) Output (Outputs — 11)

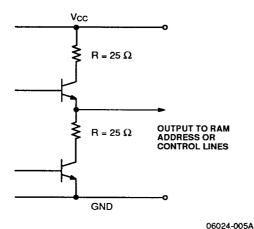
These eleven pins are the outputs from the driver.

## Vcc, GND Power, Ground Power Pair

TTL power and ground pins. The chip carrier package has two of each and the DIP has one of each.

#### **FUNCTIONAL DESCRIPTION**

Functional Description of the Am2976 is summarized on page one under General Description. For a Typical Output Driver diagram and a Function Table, refer to Figure 1 and Table 1, which follow.



**Table 1. Function Table** 

Inputs	Outputs
A <sub>0</sub> -A <sub>10</sub>	Y0-Y10
Н	Н
L	L

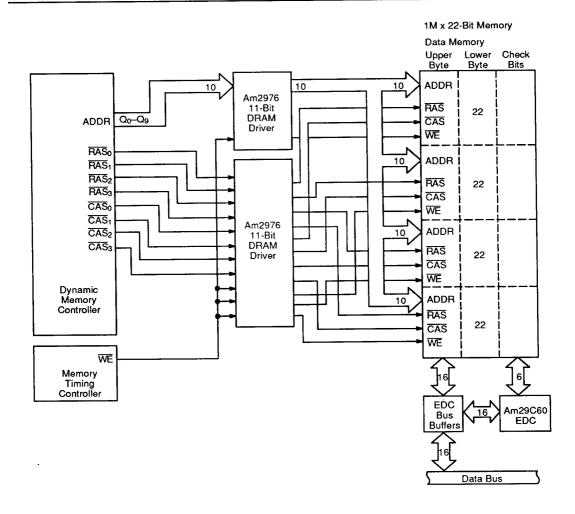
H = HIGH Key: L = LOW

Figure 1. Typical Output Driver

#### APPLICATIONS

The Am2976 is designed for use with a Dynamic Memory Controller — the Am29C668, for example — where large dynamic memories with highly capacitive input lines require additional buffering. A fully utilized memory system consists of four banks of dynamic RAMs (see Figure 2). Each bank uses identical address inputs but has individual RAS, CAS, and WE inputs. Only two de-

vices are required to drive ten address lines, four  $\overline{RAS}$  lines, four  $\overline{CAS}$  lines, and four  $\overline{WE}$  lines. Referencing Figure 2, note that the  $\overline{RAS}$  and the  $\overline{CAS}$  inputs to the memory array come from one device — thus minimizing the skew between  $\overline{RAS}$  and  $\overline{CAS}$  lines — optimizing the system's performance.



06024-006A

Figure 2. Am2976 Application Diagram

## **ABSOLUTE MAXIMUM RATINGS**

Storage Temperature -65 to +150°C

Ambient/Case Temperature

-55 to +125°C with Power Applied

Supply Voltage

with Respect to Ground -0.5 to +7.0 V

DC Voltage Applied to Outputs

for HIGH Output State

-1.5 to Vcc Max.

DC Input Voltage

--0.5 to +7.0 V

DC Output Short-Circuit Current

200 mA

DC Input Current

-30 to +5.0 mA

Stresses above those listed under Absolute Maximum Ratings may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

#### OPERATING RANGES

Commercial (C) Devices

Ambient Temperature (TA)

C to +70°C

Supply Voltage

5.0 V ± 10%

Operating ranges define those limits between which the functionality of the device is guaranteed.

## DC CHARACTERISTICS over operating ranges unless otherwise specified (Note 1)

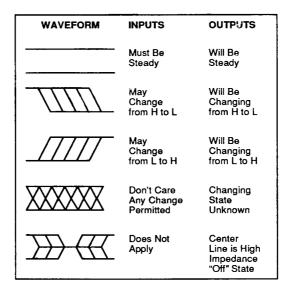
Parameter Symbol	Parameter Description	Test Condition	Min.	Max.	Unit	
VoH	Output HIGH Voltage	V <sub>CC</sub> =Min., V <sub>IN</sub> : I <sub>OH</sub> = -1 mA	2.8		٧	
Vol	Output LOW Voltage	V <sub>CC</sub> = Min.,	I <sub>OL</sub> = 1 mA		0.5	V
		$V_{IN} = V_{IH}$	I <sub>OL</sub> = 12 mA		0.8	\
ViH	Input HIGH Voltage	Guaranteed Input Logical HIGH Voltage for all Inputs		2.0		٧
VIL	Input LOW Voltage	Guaranteed Inp		0.8	٧	
Vı	Input Clamp Voltage	Vcc = Min., lin =		-1.5	٧	
I <sub>IL</sub>	Input LOW Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = 0.4 V			-0.4	mA
Iн	Input HIGH Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = 2.4 V			20	μА
l <sub>l</sub>	Input HIGH Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = 5.5 V			100	μΑ
Isc	Output Short-Circuit Current	V <sub>CC</sub> = Max. (No	V <sub>CC</sub> = Max. (Note 2)		-275	mA
Icc	Power Supply Current		T <sub>A</sub> = 0 to +70°C		90	mA

#### Notes:

- 1. For conditions shown as Min. or Max., use appropriate value as specified under Operation Ranges for applicable device type.
- 2. Not more than one output should be shorted at a time. Duration of the short-circuit test should not exceed one second.

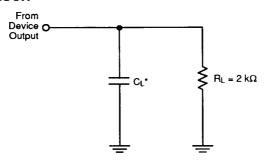
Am2976

# **KEY TO SWITCHING WAVEFORMS**



KS000010

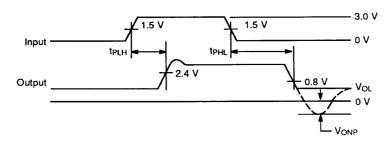
# **SWITCHING TEST CIRCUIT**



\* tpD specified at CL = 50 and 500 pF.

06024-007A

# **SWITCHING TEST WAVEFORM**



06024-008A

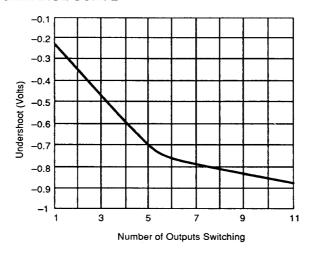
Am2976

# SWITCHING CHARACTERISTICS over operating range unless otherwise specified

No.	Parameter			1 Output Switching		11 Outputs Switching		
	Symbol	Parameter Description		Min.	Max.	Min.	Max.	Unit
C <sub>L</sub> = 50	pF							
1	tpLH	Propagation Delay from A <sub>i</sub> to Y <sub>i</sub> , LOW-to-HIGH Transition	C Devices		16		22	ns
2	t <sub>PHL</sub>	Propagation Delay from A <sub>i</sub> to Y <sub>i</sub> HIGH-LOW Transition	C Devices		12		14	ns
3	tskew	Same Transition, Output to Output (Note 1)	C Devices		5		12	ns
4	tskew	Opposite Transition, Output to Output (Note 1)	C Devices		9		16	ns
5	V <sub>ONP</sub>	Output Voltage Undershoot (Note 2)	C Devices		-0.5		-1.0	٧
C <sub>L</sub> = 500 pF								
6	t <sub>PLH</sub>	Propagation Delay from A <sub>i</sub> to Y <sub>i</sub> , LOW-HIGH Transition	C Devices		29		43	ns
7	t <sub>PHL</sub>	Propagation Delay from A <sub>i</sub> to Y <sub>i</sub> , HIGH-LOW Transition	C Devices		33		36	ns
8	tskew	Same Transition, Output to Output (Note 1)	C Devices		5		12	ns
9	tskew	Opposite Transition, Output to Output (Note 1)	C Devices		9		16	ns
10	VONP	Output Voltage Undershoot (Note 2)	C Devices		-0.5		-0.5	٧

6-148 Am2976

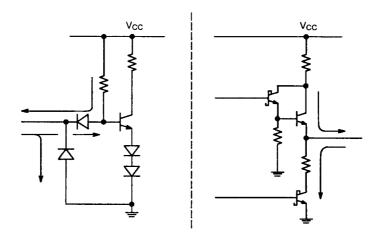
# **TYPICAL PERFORMANCE CURVE**



Undershoot vs. Outputs Switching

#### 06024-009A

# **INPUT/OUTPUT CURRENT DIAGRAM**



06024-010A

Am2976 6-149